

**ADVANCED
POWER
TECHNOLOGY®**

APT8032LNR 800V 25.0A 0.32Ω

POWER MOS IV®

AVALANCHE RATED

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT8032LNR	UNIT
V_{DSS}	Drain-Source Voltage	800	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	25	Amps
I_{DM}	Pulsed Drain Current ^①	100	
V_{GS}	Gate-Source Voltage Continuous	± 20	Volts
V_{GSM}	Gate-Source Voltage Transient	± 30	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	520	Watts
	Linear Derating Factor	4.16	W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	25	Amps
E_{AR}	Repetitive Avalanche Energy ^①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	2500	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu A$)	800			Volts
$I_{D(ON)}$	On State Drain Current ^②	APT8032LNR	25		Amps
	($V_{DS} > I_{D(ON)} \times R_{DS(ON)} \text{ Max}, V_{GS} = 10V$)				
$R_{DS(ON)}$	Drain-Source On-State Resistance ^②	APT8032LNR		0.32	Ohms
	($V_{GS} = 10V, 0.5 I_D [\text{Cont.}]$)				
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 20V, V_{DS} = 0V$)			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5mA$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.24	°C/W
$R_{\theta JA}$	Junction to Ambient			40	



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

APT8032LNR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		7500		pF
C_{oss}	Output Capacitance			700		
C_{rss}	Reverse Transfer Capacitance			250		
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		290		nC
Q_{gs}	Gate-Source Charge			30		
Q_{gd}	Gate-Drain ("Miller") Charge			125		
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		20		ns
t_r	Rise Time			30		
$t_{d(off)}$	Turn-off Delay Time			130		
t_f	Fall Time			50		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode) APT8032LNR			25	Amps
I_{SM}	Pulsed Source Current ① (Body Diode) APT8032LNR			100	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V$, $I_S = -I_D [\text{Cont.}]$)			1.3	
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)		800		ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)		16		μC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}$, $I_{DS} = P_D / 0.4 V_{DSS}$, $t = 1 \text{ Sec.}$	520			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}]$, $V_{DS} = P_D / I_D [\text{Cont.}]$, $t = 1 \text{ Sec.}$	520			
I_{LM}	Inductive Current Clamped	APT8032LNR	100			Amps

① Repetitive Rating: Pulse width limited by maximum junction temperature.

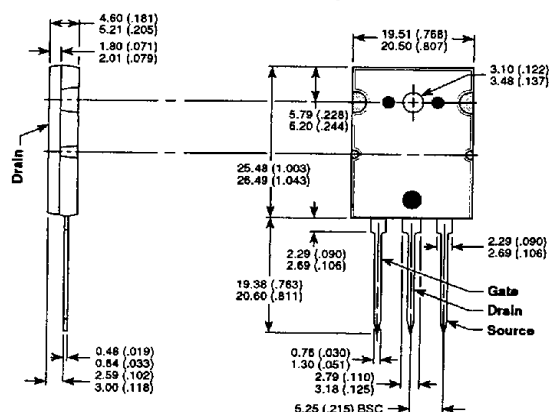
③ See MIL-STD-750 Method 3471

④ Starting $T_J = +25^\circ\text{C}$, $L = 8.00\text{mH}$, $R_G = 25\Omega$, Peak $I_L = 25A$

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

APT Reserves the right to change, without notice, the specifications and information contained herein.

TO-264AA Package Outline



Dimensions in Millimeters and (Inches)